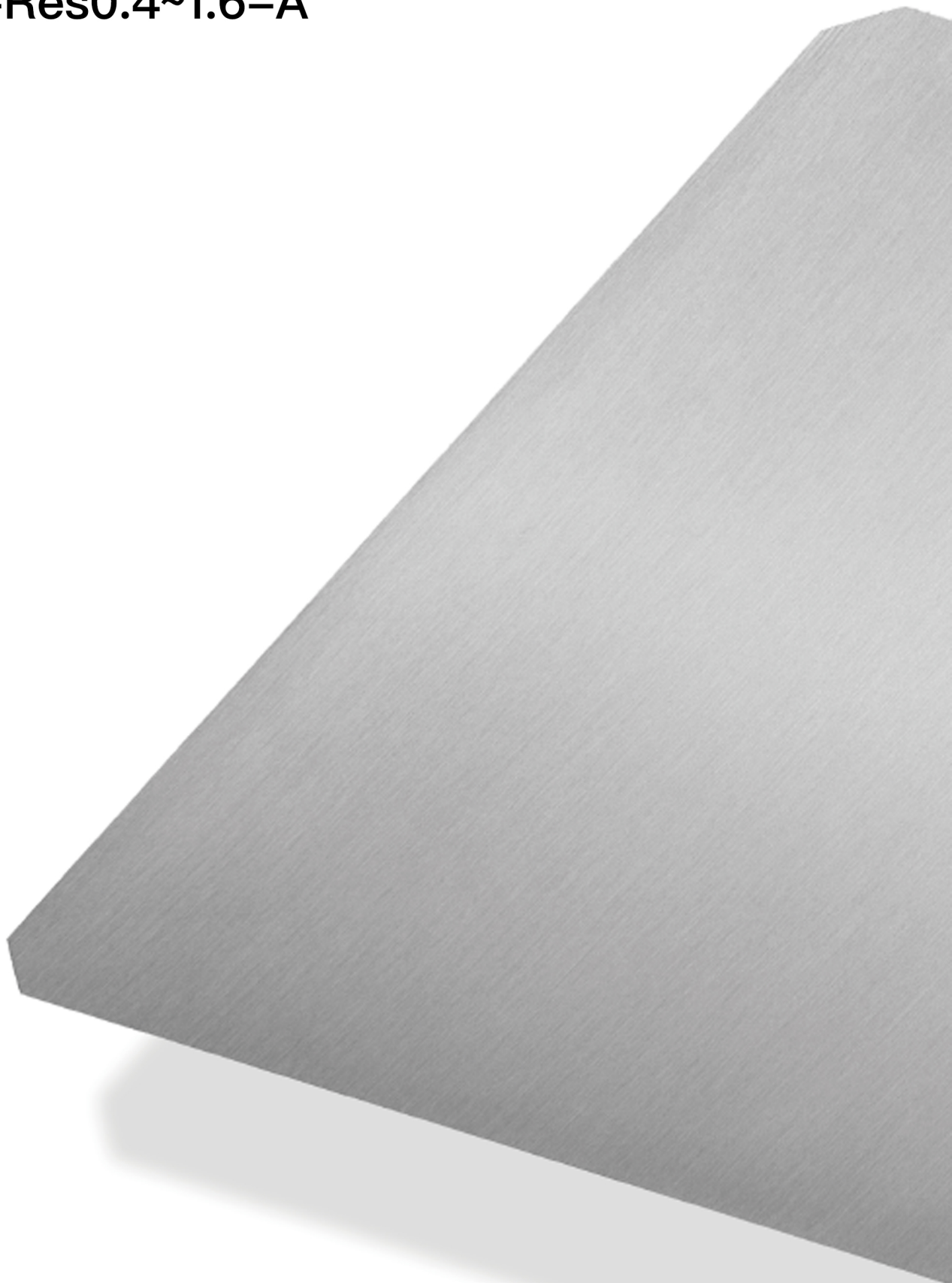


Wafer

N-type

M11-L-Res0.4~1.6-A



TOP PV TECH,
DRIVING ONWARD FOR GREEN ENERGY

Monocrystalline Silicon Wafer Specification

N-type-M11-L-Res 0.4~1.6-Grade A

Key Parameters

Conductive Type	N-type	P/N Type Tester (DLY – 2 P/N)
Doping Element	Phos. (Phosphorus)	--
Resistivity/ $\Omega \cdot \text{cm}$	0.4–1.6	Silicon Wafer Automatic Testing Equipment
Minority Carrier Lifetime/ μs	≥ 1000	Transient Photoconductance Decay Method
Interstitial Oxygen Content/ at/cm^3	$\leq 6.0 \times 10^{17}$	Fourier Transform Infrared Spectrometer (ASTM F121–83)
Substitutional Carbon Content/ at/cm^3	$\leq 5.0 \times 10^{16}$	Fourier Transform Infrared Spectrometer (GB/T1558–2009)

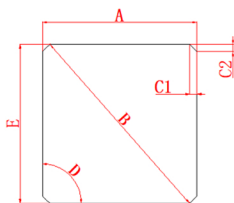
Material Properties

Growth Method	Czochralski Method	--
Crystallinity	Single Crystal	--
Dislocation Density/ pcs/cm^2	≤ 500	Preferred Chemical Etching Method (ASTM F47–88)
Surface Crystal Orientation/ $^\circ$	$<100> \pm 3$	X-ray Diffractometer (ASTM F26–1987)
Side Crystal Orientation/ $^\circ$	$<010>, <001> \pm 3$	X-ray Diffractometer (ASTM F26–1987)

Geometric Dimensions and Surface Properties

Silicon Wafer Model	M11-L	--
Geometric Shape	Standard	--
Chamfered Edge Shape	Rounded	--
Silicon Wafer Edge Distance/mm	Short side 182.2 ± 0.25 ; Long side 191.6 ± 0.25	Silicon Wafer Automatic Testing Equipment
Silicon Wafer Diameter/mm	$\Phi 262.5 \pm 0.25$	Silicon Wafer Automatic Testing Equipment
Arc Length Projection/mm	C1: 1.38 ± 0.5 ; C2: 1.32 ± 0.5	Silicon Wafer Automatic Testing Equipment
Perpendicularity/ $^\circ$	90 ± 0.15	Silicon Wafer Automatic Testing Equipment
Thickness/ μm	130 ± 8	Silicon Wafer Automatic Testing Equipment
Batch Thickness/ μm	≥ 130	Silicon Wafer Automatic Testing Equipment
TTV/ μm	≤ 20	Silicon Wafer Automatic Testing Equipment
Scratch/ μm	≤ 13	Silicon Wafer Automatic Testing Equipment
Warpage/ μm	≤ 40	Silicon Wafer Automatic Testing Equipment
Bow/ μm	≤ 40	Silicon Wafer Automatic Testing Equipment
Cutting Method	Diamond Wire Cutting	--
Surface Quality	The surface is clean, with no visible pollution, and color deviation (judged according to standard sample pieces)	Silicon Wafer Automatic Testing Equipment
Edge Chipping	Depth $\leq 0.3\text{mm}$ & Length $\leq 0.5\text{mm}$, no more than 1 piece, no V-shaped edge chipping	Manual Inspection or Silicon Wafer Automatic Testing Equipment
Hidden Cracks/Pores	Not Allowed	Silicon Wafer Automatic Testing Equipment

Schematic diagram of silicon wafer dimensions



Size: M11-L

A: $182.2 \pm 0.25\text{mm}$

E: $191.6 \pm 0.25\text{mm}$

B: $\Phi 262.5 \pm 0.25\text{mm}$

C1: $1.38 \pm 0.5\text{mm}$

C2: $1.32 \pm 0.5\text{mm}$

D: $90 \pm 0.15^\circ$